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(71) Applicant: MICRON TECHNOLOGY, INC. [US/US];

MS 1-525 8000 South Federal Way, Boise, ID 83716 (US).

(72) Inventors: **LUO, Shuangqiang**; 5620 S. Zonetailed Way, Boise, ID 83716 (US). **CHARY, Indra, V.**; 1168 E. Opus Street, Boise, ID 83716 (US). **DORHOUT, Justin, B.**; P.O. Box 8023, Boise, ID 83707 (US). **KLEIN, Rita, J.**; 11336 W. Divide Pass Drive, Boise, ID 83709 (US).

(74) Agent: **TAYLOR, Jennifer, J.**; Wells St. John P.S., 601 W. Main Avenue, Suite 600, Spokane, WA 99201 (US).

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(54) Title: INTEGRATED ASSEMBLIES HAVING CONDUCTIVE POSTS EXTENDING THROUGH STACKS OF ALTERNATING MATERIALS

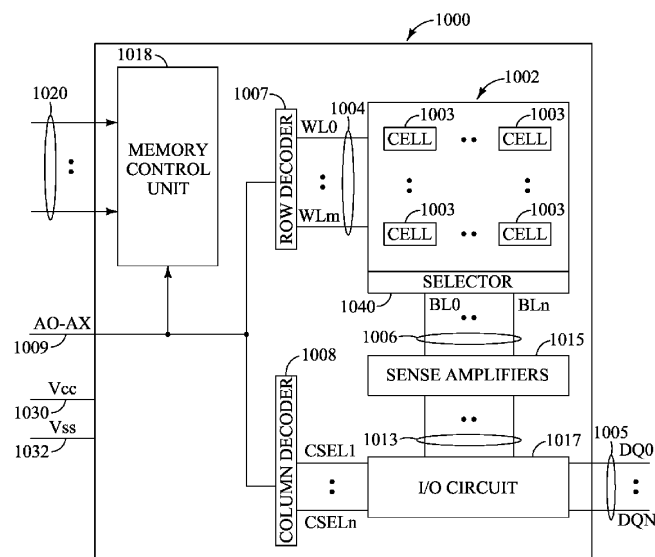


FIG. 1
Prior Art

(57) Abstract: Some embodiments include an integrated assembly having a conductive expanse over conductive nodes. The conductive nodes include a first composition. A bottom surface of the conductive expanse includes a second composition which is different composition than the first composition. A stack is over the conductive expanse. The stack includes alternating first and second levels. Pillar structures extend vertically through the stack. Each of the pillar structures includes a post of conductive material laterally surrounded by an insulative liner. At least one of the posts extends through the conductive expanse to directly contact one of the conductive nodes. Some embodiments include methods of forming integrated assemblies.

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